

Silicon planer type (cathode common)

For switching

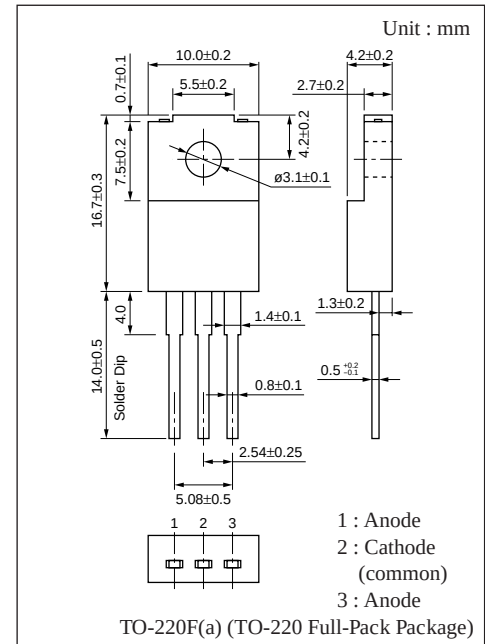
■ Features

- High reverse voltage V_R
- Low forward voltage V_F
- Fast reverse recovery time t_{rr}

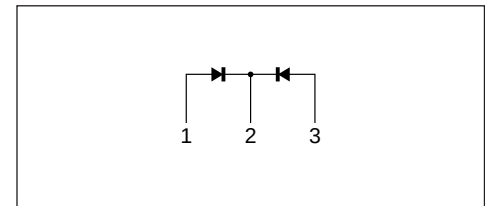
■ Absolute Maximum Ratings (Ta= 25°C)

Parameter	Symbol	Rating	Unit
Repetitive peak reverse voltage	V_{RRM}	200	V
Non-repetitive peak reverse voltage	V_{RSM}	200	V
Average forward current	$I_{F(AV)}$	10	A
Non-repetitive peak forward surge current	I_{FSM}^*	60	A
Junction temperature	T_j	- 40 to +150	°C
Storage temperature	T_{stg}	- 40 to +150	°C

* Sine half wave : 10ms/cycle



■ Internal Connection

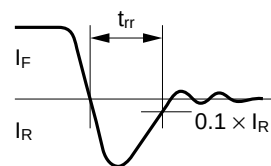
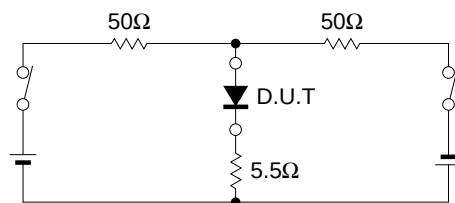


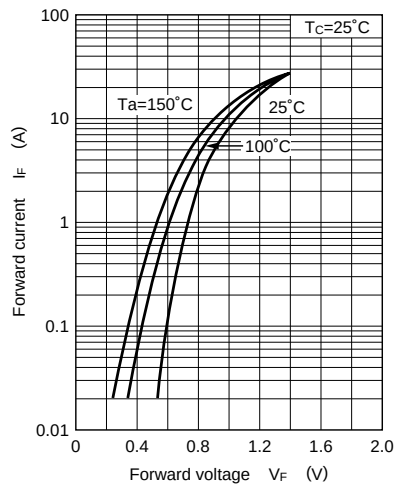
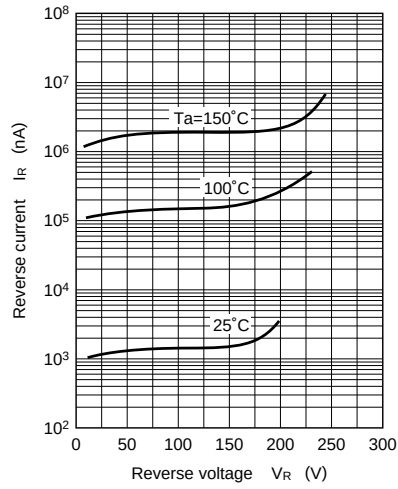
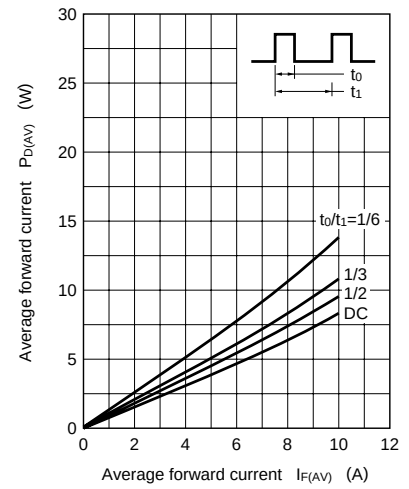
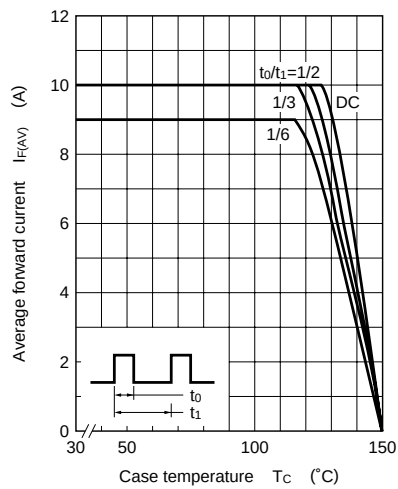
■ Electrical Characteristics (Ta= 25°C)

Parameter	Symbol	Condition	min	typ	max	Unit
Repetitive peak reverse current	I_{RRM1}	$V_{RRM}= 200V, T_C= 25^{\circ}C$			100	μA
	I_{RRM2}	$V_{RRM}= 200V, T_J=150^{\circ}C$			6	mA
Forward voltage (DC)	V_F	$I_F= 5A, T_C= 25^{\circ}C$			1	V
Reverse recovery time	t_{rr}^{*}	$I_F=1A, I_R=1A$			100	ns
Thermal resistance	$R_{th(j-c)}$	Flat direct current between junction and case			3	$^{\circ}C/W$
	$R_{th(j-a)}$				63	$^{\circ}C/W$

Note 1. Rated input/output frequency : 10MHz

2. * t_{IT} measuring circuit



$I_F - V_F$  $I_R - V_R$  $P_{D(AV)} - I_{F(AV)}$  $I_{F(AV)} - T_C$  $R_{th(t)} - t$ 